

TOSHIBA GTR MODULE SILICON N CHANNEL IGBT

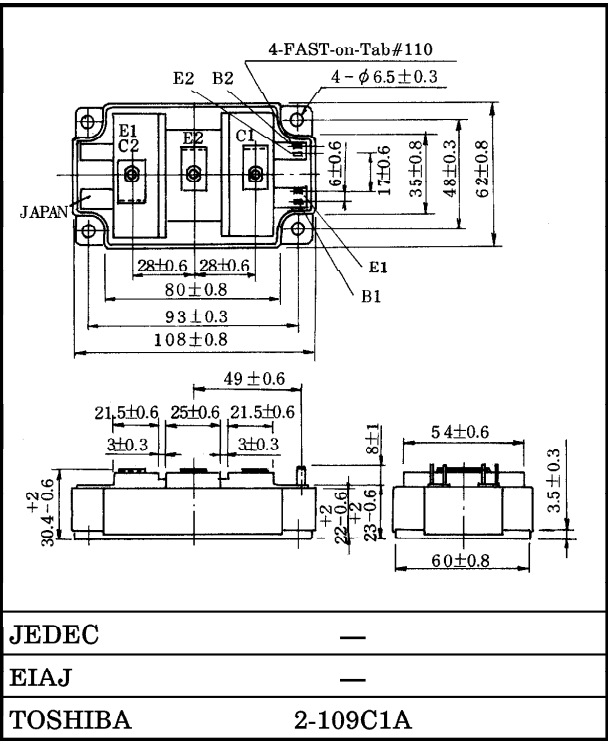
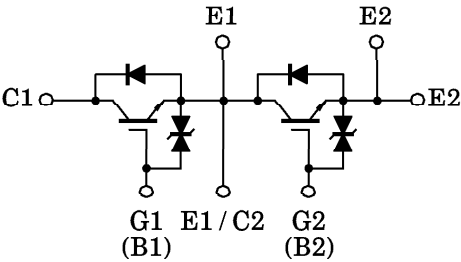
MG150Q2YS40

HIGH POWER SWITCHING APPLICATIONS.
MOTOR CONTROL APPLICATIONS.

Unit in mm

- High Input Impedance
- High Speed : $t_f=0.5\mu s$ (Max.)
 $t_{rr}=0.5\mu s$ (Max.)
- Low Saturation Voltage : $V_{CE(sat)}=4.0V$ (Max.)
- Enhancement-Mode
- Includes a Complete Half Bridge in One Package.
- The Electrodes are Isolated from Case.

EQUIVALENT CIRCUIT



Weight : 430g

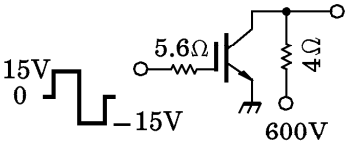
MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	RATING	UNIT
Collector-Emitter Voltage		V_{CES}	1200	V
Gate-Emitter Voltage		V_{GES}	± 20	V
Collector Current	DC	I_C	150	A
	1ms	I_{CP}	300	
Forward Current	DC	I_F	150	A
	1ms	I_{FM}	300	
Collector Power Dissipation (Tc = 25°C)		P_C	1100	W
Junction Temperature		T_j	150	°C
Storage Temperature Range		T_{stg}	-40~125	°C
Isolation Voltage		V_{Isol}	2500 (AC 1 minute)	V
Screw Torque (Terminal / Mounting)		—	3 / 3	N · m

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ELECTRICAL CHARACTERISTICS ($T_a = 25^\circ\text{C}$)

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Gate Leakage Current		I_{GES}	$V_{\text{GE}} = \pm 20\text{V}$, $V_{\text{CE}} = 0$	—	—	± 20	μA
Collector Cut-off Current		I_{CES}	$V_{\text{CE}} = 1200\text{V}$, $V_{\text{GE}} = 0$	—	—	2.0	mA
Gate-Emitter Cut-off Voltage		$V_{\text{GE(OFF)}}$	$I_{\text{C}} = 150\text{mA}$, $V_{\text{CE}} = 5\text{V}$	3.0	—	6.0	V
Collector-Emitter Saturation Voltage		$V_{\text{CE(sat)}}$	$I_{\text{C}} = 150\text{A}$, $V_{\text{GE}} = 15\text{V}$	—	3.0	4.0	V
Input Capacitance		C_{ies}	$V_{\text{CE}} = 10\text{V}$, $V_{\text{GE}} = 0$ $f = 1\text{MHz}$	—	18000	—	pF
Switching Time	Rise Time	t_{r}		—	0.3	0.6	μs
	Turn-on Time	t_{on}		—	0.4	0.8	
	Fall Time	t_{f}		—	0.2	0.5	
	Turn-off Time	t_{off}		—	0.8	1.5	
Forward Voltage		V_{F}	$I_{\text{F}} = 150\text{A}$, $V_{\text{GE}} = 0$	—	2.0	3.0	V
Reverse Recovery Time		t_{rr}	$I_{\text{F}} = 150\text{A}$, $V_{\text{GE}} = -10\text{V}$ $di / dt = 200\text{A} / \mu\text{s}$	—	0.25	0.5	μs
Thermal Resistance		$R_{\text{th(j-c)}}$	Transistor	—	—	0.11	$^\circ\text{C} / \text{W}$
			Diode	—	—	0.4	

